

[METHOD OF FORMING GAS DIELECTRIC WITH SUPPORT STRUCTURE]

Abstract

A method for forming a gas dielectric with support structure on a semiconductor device structure provides low capacitance and adequate support for a conductor of the semiconductor device structure. A conductive structure, such as via or interconnect, is formed in a wiring-layer dielectric. A support is then formed that connects to the conductive structure, the support including an area thereunder. The wiring-layer dielectric is then removed from the area to form a gas dielectric.